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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/705,223	11/12/2003	Yasuo Segawa	492322014700	3537
25227 7	7590 01/13/2005		EXAMINER	
MORRISON & FOERSTER LLP			QUINTO, KEVIN V	
1650 TYSONS SUITE 300	BOULEVARD		ART UNIT	PAPER NUMBER
MCLEAN, V	A 22102		2826	
			DATE MAILED: 01/13/2005	

Please find below and/or attached an Office communication concerning this application or proceeding.

		Me -
	Application No.	Applicant(s)
Office Action Cumman.	10/705,223	SEGAWA ET AL.
Office Action Summary	Examiner	Art Unit
The SAAU INC DATE of this communication and	Kevin Quinto	2826
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the t	correspondence address
A SHORTENED STATUTORY PERIOD FOR REPL' THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply If NO period for reply is specified above, the maximum statutory period of Failure to reply within the set or extended period for reply will, by statute Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be tir y within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from , cause the application to become ABANDONE	nely filed s will be considered timely. the mailing date of this communication. D (35 U.S.C. § 133).
Status	•	
 1) Responsive to communication(s) filed on 22 O 2a) This action is FINAL. 2b) This 3) Since this application is in condition for alloware closed in accordance with the practice under E 	action is non-final. nce except for formal matters, pro	
Disposition of Claims		
 4) ☐ Claim(s) 1-11 is/are pending in the application. 4a) Of the above claim(s) is/are withdraw 5) ☐ Claim(s) 8-11 is/are allowed. 6) ☐ Claim(s) 1,3 and 6 is/are rejected. 7) ☐ Claim(s) 2,4,5 and 7 is/are objected to. 8) ☐ Claim(s) are subject to restriction and/o 	wn from consideration.	
Application Papers		
9) The specification is objected to by the Examine 10) The drawing(s) filed on is/are: a) accomplicated any not request that any objection to the Replacement drawing sheet(s) including the correct 11) The oath or declaration is objected to by the Examine	epted or b) objected to by the liderawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	e 37 CFR 1.85(a). jected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the priori	s have been received. s have been received in Applicati rity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National Stage
* See the attached detailed Office action for a list	of the certified copies not receive	ed.
140-ch(c)		
Attachment(s) Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	

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DETAILED ACTION

Response to Arguments

1. Applicant's arguments with respect to claims 1-7 have been considered but are moot in view of the new ground(s) of rejection.

Claim Rejections - 35 USC § 102

2. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

- (b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on sale in this country, more than one year prior to the date of application for patent in the United States.
- 3. Claims 1, 3, and 6 are rejected under 35 U.S.C. 102(b) as being anticipated by Hsu et al. (USPN 5,880,991).
- 4. In reference to claims 1 and 6, Hsu et al. (USPN 5,880,991, hereinafter referred to as the "Hsu" reference) discloses a similar device. Figures 5a-5l illustrate an n-channel or p-channel thin film transistor formed on a substrate. Figures 5a-5l show a storage capacitor disposed adjacent the thin film transistor and keeping a voltage supplied through the thin film transistor. A first semiconductor portion (the SOI layer for the DRAM cell) makes a first capacitance coupling with a gate electrode of the thin film transistor. A second semiconductor portion (the lower capacitor electrode in the DRAM cell portion) makes a second capacitance coupling with a storage capacitor electrode (the upper capacitor electrode in the DRAM cell portion). The second semiconductor

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portion is not in physical contact with the first semiconductor portion. A wiring (the metal wiring directly connected to the lower capacitor electrode) connects the first semiconductor portion to the second semiconductor portion. The second semiconductor portion is between the substrate and the storage capacitor electrode.

5. In reference to claim 3, figures 5a-5l show that the storage capacitor electrode is parallel to the gate electrode.

Allowable Subject Matter

- 6. Claims 8-11 were allowed in the previous Office action.
- 7. Claims 2, 4, 5 and 7 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.
- 8. The following is a statement of reasons for the indication of allowable subject matter: the examiner is unaware of any prior art which suggests a semiconductor device with a thin film transistor and a capacitor constructed such that that the thin film transistor and the capacitor each have a component made of semiconductor film, these films being two spaced apart bodies, formed directly on the surface of the substrate such that these films are electrically coupled together by a metal wiring.

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Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Kevin Quinto whose telephone number is (571) 272-1920. The examiner can normally be reached on M-F 8AM-5PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

KVQ

SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800